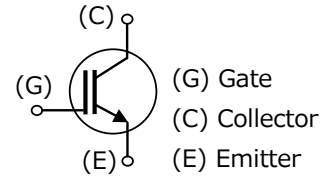




MMJC575A01**



Outline

IGBT (Bare chip) utilizes various technologies that we cultivated by analog semiconductor device production and is the product which prepared a lineup of the wide high voltage, high current which can contribute to high efficiency and saving energy.

Applications

- Industrial Motor Drivers
- Inverter
- Welding
- UPS

Features

- ① Field Stop Trench gate IGBT
- ② Low Collector-Emitter saturation voltage
- ③ High short circuit capability
- ④ Low switching losses

Absolute Maximum Ratings

T_j=25deg unless otherwise noted.

Parameter	Symbol	Rating	Unit
Collector-Emitter voltage	VCES	1250	V
Gate-Emitter voltage	VGES	±30	V
Collector current *1)	IC	75	A
Junction temperature	T _j	-40~+175	°C

*1)Collector current is limited by T_j(max) and thermal properties of assembly.

Die Specification

Item	Value	Unit
Die thickness	140	μm
Die size	7.9x7.9(62.4)	mm
Front metal(AlSi)	6.5	μm
Backside metal(AlSi/Ti/Ni/Au)	1.45	μm

Electrical Characteristics

T_j=25deg unless otherwise noted.

Parameter	Symbol	Specification			Unit	condition	
		Min	Typ	Max			
Zero gate voltage collector current	ICES	-	-	1	μA	V _{ce} =1250V, V _{ge} =0V	
Gate-Emitter leakage current	IGES	-	-	±500	nA	V _{ge} =±30V, V _{ce} =0V	
Gate-emitter threshold voltage	VGE(th)	5.00	-	6.80	V	V _{ce} =10V, I _c =2.5mA	
Collector-Emitter saturation voltage	T _j =25°C	VCE	-	1.85	2.15	V	I _c =75A, V _{ge} =15V
	T _j =175°C	(sat)	-	2.25	-		
Input capacitance	Cies	-	7500	-	pF	VCE=25V, VGE=0V, f=1MHz	
Switching time *Reference characteristics	td(on)	-	33	-	ns	V _{cc} =600V, I _c =75A	
	tr	-	40	-	ns	VGE=-15/+15V, Rg=12Ω, Inductive load, Ls≧110nH	
	td(off)	-	280	-	ns		
	tf	-	260	-	ns		
Short circuit withstand time	Tsc	10	-	-	μs	V _{cc} =720V, V _{ge} =15V, T _j =150°C	

This characteristic is when it is incorporated in a mold package or evaluation board.

Depending on the assembly conditions etc., it may not be satisfied. Please note that it is not a guaranteed value.

Die Dimension

